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Sheet 1 of 1

<p>(Rev. 5/92) Comparable to Form PTO-1449</p>	<p>U.S. Department of Commerce Patent and Trademark Office</p>	<p>Atty. Docket No.</p>	<p>Serial No.</p>
		<p>86397</p>	<p>not yet assigned</p>
<p>INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)</p>			
<p>Applicants Satoshi Komiya et al.</p>			
<p>Filing Date: herewith</p>		<p>Group</p>	

U.S. PATENT DOCUMENTS

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
<i>MM</i>		5,935,320	08/10/1999	GRAEF ET AL.	<i>✓</i>		

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		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

		International Search Report (date of mailing 24.10.2000) which issued in connection with above cited references
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Examiner <i>ell</i>	Date Considered <i>5/30/03</i>
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Applicable to
Form PTO-1449U.S. Department of Commerce
Patent and Trademark OfficeAtty. Docket No.
86397Serial No.
10/049,875

INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Applicants

Satoshi Komiya et al.

Filing Date

February 12, 2002

Group

Unassigned

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*Ex. Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate

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		Document Number	Date	Country	Class	Subclass	Translation	
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	C2	Ciszek et al.; "Effect of Nitrogen Doping on Microdefects and Minority Charge Carrier Lifetime of High-Purity, Dislocation-Free and Multicrystalline Silicon," <i>Solar Energy Materials and Solar Cells</i> , Vol. 41/42, 1996, pp. 61-70 (XP 000614222)
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*Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.